



General Description

The MAX8568A/MAX8568B backup-battery-management ICs are complete charging and backup switchover control solutions for PDAs, Smart Phones, and other smart portable devices. They charge both NiMH and rechargeable lithium battery types and feature programmable charge current and termination voltage. Separate optimized charge algorithms for both lithium and NiMH cells are included on-chip.

The MAX8568A/MAX8568B also manage backup switchover from a primary power source. An accurate onchip voltage detector monitors the main supply and backs up two system supplies (typically I/O and memory) when main power falls. On-chip drivers switch external MOSFETs to disconnect the main supply from the system loads so the backup source is not drained.

Low-voltage backup cells can be stepped up by an onchip synchronous-rectified, low-quiescent-current boost converter. Additionally, a low-quiescent-current LDO generates a second backup voltage. The MAX8568A LDO is preset to 2.5V while the MAX8568B LDO is preset to 1.8V. Both devices are supplied in 16-pin 3mm x 3mm thin QFN packages rated for -40°C to +85°C operation.

Applications

PDAs and PDA Phones

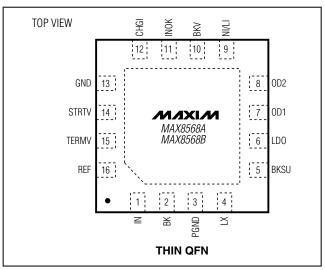
Smart Phones

DSCs and DVCs

Palmtops and Wireless Handhelds

Internet Appliances and Web-Books

Pin Configuration



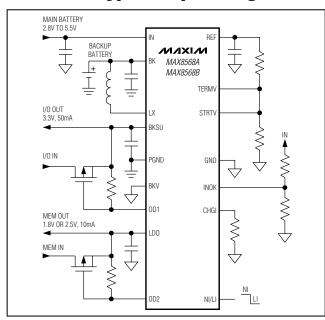
Features

- ♦ Automatically Manage All Backup Switchover **Functions**
- ♦ Charge Both NiMH and Rechargeable Lithium **Backup Batteries**
- ♦ On-Chip Battery Boost Converter for 1-Cell NiMH
- ♦ Two Backup Output Voltages
- **♦ Programmable Charge Current**
- **♦ Programmable Charge Voltage Limit**
- ♦ Low 17µA Operating Current in Backup Mode
- **♦ Eliminate Many Discrete Components**
- ◆ Tiny 3mm x 3mm Thin QFN Package

Ordering Information

PART	TEMP RANGE	PIN- PACKAGE	TOP MARK
MAX8568AETE	-40°C to +85°C	16 Thin QFN 3mm x 3mm (T1633-4)	ACK
MAX8568BETE	-40°C to +85°C	16 Thin QFN 3mm x 3mm (T1633-4)	ACL

Typical Operating Circuit



NIXIN

Maxim Integrated Products 1

ABSOLUTE MAXIMUM RATINGS

IN, BK, BKSU, OD1, OD2 to GND.	0.3V to +6.0V
BKV, LDO, NI/LI to GND	0.3V to (V _{BKSU} + 0.3V)
REF, CHGI, INOK, TERMV, STRTV	to GND0.3V to (V _{IN} + 0.3V)
PGND to GND	0.3V to + 0.3V
LX Current	0.9A _{RMS}

Continuous Power Dissipation (T _A = +70°	C)
16-Pin 3mm x 3mm Thin QFN	
(derate 15.6mW/°C above +70°C)	1250mW
Operating Temperature Range	40°C to +85°C
Junction Temperature	+150°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (soldering, 10s)	+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

(Circuit of Figure 7, $V_{IN} = V_{INOK} = 3.6V$, $V_{BK} = 1.4V$, $V_{NI/LI} = V_{BKSU} = 3.3V$, $V_{BKV} = GND = PGND = 0V$, $V_{STRTV} = V_{TERMV} = 1.2V$, $R5 = 250k\Omega$, $T_{A} = 0^{\circ}C$ to $+85^{\circ}C$, unless otherwise noted. Typical values are at $T_{A} = +25^{\circ}C$.) (Note 1)

PARAMETER	PARAMETER CONDITIONS				MAX	UNITS	
IN Voltage Range			2.8		5.5	V	
		T _A = +25°C		3	5		
IN Operating Current	Charger off, V _{INOK} = 1.5V	T _A = +85°C		3		μΑ	
	Charger on, not including ch	narge current		50	90		
CHGI Current Limit	$R_{CHGI} = 169k\Omega$, $V_{BK} = 1.3V$	r	8	10	12	mA	
CHGI Bias Voltage				600		mV	
CHGI Resistor Range	V _{BK} = 1.3V		50		1800	kΩ	
	$V_{IN} = 5.5V, V_{NI/LI} = 0V$		4.116	4.2	4.284		
BK Charge Voltage Limit	$V_{IN} = 3.8V$, $V_{NI/LI} = 0V$, V_{TEF}	_{RMV} = 1V	3.42	3.5	3.58	V	
	$V_{IN} = V_{NI/LI} = 3.6V$	1.746	1.8	1.854			
BK Reverse Leakage Current to IN	$V_{IN} = 0V$	$T_A = +25^{\circ}C$		0.01	0.5	μΑ	
BK neverse Leakage Current to IIV	VIN = OV	$T_A = +85^{\circ}C$		0.1			
NiMH Mode BK High Threshold Voltage, VBK(NIHI)	V _{TERMV} = 1.2V		1.37	1.4	1.43	V	
NiMH Mode BK Low Threshold Voltage, VBK(NILO)	V _{STRTV} = 1.2V		1.17	1.2	1.23	V	
TEDAN/ Inquit Coursest	\/ 4.4\/	$T_A = +25^{\circ}C$		0.001	0.05	μΑ	
TERMV Input Current	V _{TERMV} = 1.1V	T _A = +85°C		0.01			
CTDT) / In result Course ret	V 1 1V	T _A = +25°C		0.001	0.05		
STRTV Input Current	$V_{STRTV} = 1.1V$ $T_{A} = +85^{\circ}$			0.01		μA	
REF Output Voltage	I _{REF} = 1µA		1.23	1.25	1.27	V	
REF Load Regulation	$I_{REF} = 1\mu A \text{ to } 50\mu A$			2.5	10	mV	
REF Line Regulation	$V_{IN} = 3V$ to 5.5V, $I_{REF} = 1\mu A$	1		1	7	mV	
INOV Threshold Voltage	V _{INOK} falling	2.38	2.43	2.48	V		
INOK Threshold Voltage	V _{INOK} rising	2.40	2.47	2.54			
INOK Input Current	VINION = 2V	$T_A = +25^{\circ}C$		0.005	0.1	μΑ	
IIION IIIpat Oullellt	VINUK - ZV	$V_{\text{INOK}} = 2V$ $T_{\text{A}} = +85^{\circ}\text{C}$		0.05		μΑ	
NI/LI Logic-Level High	V _{BKSU} = 3.3V		1.8			V	
NI/LI Logic-Level Low	V _{BKSU} = 3.3V				0.4	V	

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ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 7, $V_{IN} = V_{INOK} = 3.6V$, $V_{BK} = 1.4V$, $V_{NI/LI} = V_{BKSU} = 3.3V$, $V_{BKV} = GND = PGND = 0V$, $V_{STRTV} = V_{TERMV} = 1.2V$, $R5 = 250k\Omega$, $T_A = 0^{\circ}C$ to $+85^{\circ}C$, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$.) (Note 1)

PARAMETER	CONDITIONS	CONDITIONS				UNITS	
NI/I I located Comment	V 0.0V	T _A = +25°C		0.05	1	^	
NI/LI Input Current	$V_{BKSU} = V_{NI/LI} = 3.3V$	T _A = +85°C		0.1		μΑ	
OD_ On-Resistance	V _{BKSU} = 3.6V			11	30	Ω	
OD_ Leakage Current	V _{OD} = 5.5V	$T_A = +25^{\circ}C$		0.01	1	μΑ	
OD_ Leakage Current	VOD_ = 0.5V	$T_A = +85^{\circ}C$		0.1		μΑ	
BACKUP STEP-UP (Note 2)							
BK Input Undervoltage Lockout	V _{NI/LI} = 0V, falling trip point			2.45		V	
BIT IIIput Olidervoltage Lockout	$V_{NI/LI} = V_{BKSU} = 3.3V$, falling	g trip point	1.05	1.12	1.21	V	
BK Input Voltage					5.5	V	
Quiescent Current into BKSU	I _{LDO} = 0mA, not switching			17	25	μΑ	
Quiescent Current into BK	I _{BKSU} = I _{LDO} = 0mA, not sw	_		2.4	4	μΑ	
Shutdown Current into BK	V _{IN} = V _{INOK} = V _{BKSU} = 0V	$T_A = +25^{\circ}C$		0.001	0.5	μA	
Shaldown Carrent into Bix	AIM - AIMOK - ABK20 - OA	$T_A = +85^{\circ}C$	0.1			μΑ	
BKV Feedback Voltage			1.162	1.21	1.258	V	
BKV Feedback Bias Current	V _{BKV} = 1V	$T_A = +25^{\circ}C$		5	50	nA	
DIVI FEEDBACK DIAS CUITETIL	ABVA — 1A	$T_A = +85^{\circ}C$		10			
BKSU Output-Voltage Accuracy	$V_{BKV} = 0V$	3.17	3.3	3.43	V		
Divide Output Voltage / tecuracy	V _{BKV} = V _{BKSU}	2.4	2.5	2.6	V		
BKSU Output Voltage Range			2.5		5	V	
n-Channel Switch On-Resistance	$I_{LX} = 200 \text{mA}$			0.4	1	Ω	
p-Channel Switch On-Resistance	$I_{LX} = 200 \text{mA}$			0.7	2	Ω	
LX Leakage Current	$T_A = +25^{\circ}C$		0.05	1	μΑ		
EX Edukage Outlett	$T_A = +85^{\circ}C$		0.1				
LX Current Limit (ILIM)			400	500	600	mA	
n-Channel Switch Maximum On-Time		3.5	5	6.5	μs		
p-Channel Zero-Channel Crossing Current			5	20	35	mA	
LOW-DROPOUT REGULATOR	1						
BKSU Input Voltage Range			2.7		5.0	V	
LDO Output-Voltage Accuracy	V _{BKSU} = 3.3V		2.375	2.5	2.625	V	
, ,		MAX8568B	1.71 1.8		1.89	V	
LDO Line Regulation	$2.7V < V_{BKSU} < 5V$, $I_{LDO} = 1$	ImA		1		mV	
LDO Load Regulation	$1\mu A < I_{LDO} < 10mA$			2.5		mV	

ELECTRICAL CHARACTERISTICS

(Circuit of Figure 7, $V_{IN} = V_{INOK} = 3.6V$, $V_{BK} = 1.4V$, $V_{NI/LI} = V_{BKSU} = 3.3V$, $V_{BKV} = GND = PGND = 0V$, $V_{STRTV} = V_{TERMV} = 1.2V$, $R5 = 250k\Omega$, $T_A = -40^{\circ}C$ to $+85^{\circ}C$, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$.) (Note 3)

PARAMETER	CONDITIONS	MIN	MAX	UNITS		
IN Voltage Range		2.8	5.5	V		
IN Operating Current	Charger on, not including charge current		90	μΑ		
CHGI Current Limit	$R_{CHGI} = 169k\Omega$, $V_{BK} = 1.3V$	8	12	mA		
CHGI Resistor Range	V _{BK} = 1.3V	50	1800	kΩ		
	$V_{IN} = 5.5V, V_{NI/LI} = 0V$	4.116	4.310			
BK Charge Voltage Limit	$V_{IN} = 3.8V$, $V_{NI/LI} = 0V$, $V_{TERMV} = 1V$	3.420	3.605	V		
	$V_{IN} = V_{NI/LI} = 3.6V$	1.746	1.854			
NiMH Mode BK High Threshold Voltage, VBK(NIHI)	V _{TERMV} = 1.2V	1.37	1.43	V		
NiMH Mode BK Low Threshold Voltage, VBK(NILO)	V _{STRTV} = 1.2V	1.17	1.23	V		
REF Output Voltage	I _{REF} = 1µA	1.225	1.275	V		
REF Load Regulation	I _{REF} = 1μA to 50μA		10	mV		
REF Line Regulation	$V_{IN} = 3V \text{ to } 5.5V, I_{REF} = 1\mu A$		7	mV		
INIOI/ Threehold Voltage	V _{INOK} falling	2.38	2.48	V		
INOK Threshold Voltage	V _{INOK} rising	2.40	2.54	V		
NI/LI Logic-Level High	$V_{BKSU} = 3.3V$	1.8		V		
NI/LI Logic-Level Low	$V_{BKSU} = 3.3V$		0.4	V		
OD_ On-Resistance	$V_{BKSU} = 3.6V$		30	Ω		
BACKUP STEP-UP (Note 2)						
BK Input Undervoltage Lockout	V _{NI/LI} = V _{BKSU} = 3.3V, falling trip point	1.05	1.21	V		
BK Input Voltage			5.5	V		
Quiescent Current into BKSU	I _{LDO} = 0mA, not switching		25	μΑ		
Quiescent Current into BK	I _{BKSU} = I _{LDO} = 0mA, not switching		4	μΑ		
BKV Feedback Voltage		1.162	1.258	V		
DKSLL Output Voltage Acquire ov	$V_{BKV} = 0V$	3.17	3.43	\/		
BKSU Output-Voltage Accuracy	V _{BKV} = V _{BKSU}	2.4	2.6	.6 V		
BKSU Output Voltage Range		2.5	5.0	V		
n-Channel Switch On-Resistance	$I_{LX} = 200 \text{mA}$		1	Ω		
p-Channel Switch On-Resistance	$I_{LX} = 200 \text{mA}$		2	Ω		

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ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 7, $V_{INOK} = 3.6V$, $V_{BK} = 1.4V$, $V_{NI/LI} = V_{BKSU} = 3.3V$, $V_{BKV} = GND = PGND = 0V$, $V_{STRTV} = V_{TERMV} = 1.2V$, $R5 = 250k\Omega$, $T_A = -40^{\circ}C$ to $+85^{\circ}C$, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$.) (Note 3)

PARAMETER	CON	IDITIONS		MIN	MAX	UNITS
LX Current Limit (ILIM)				400	600	mA
n-Channel Switch Maximum On-Time				3.5	6.5	μs
p-Channel Zero-Channel Crossing Current				5	35	mA
LOW-DROPOUT REGULATOR						
BKSU Input Voltage Range				2.7	5.0	V
L DO Output Voltage Assurage	V 2 2V		MAX8568A	2.375	2.625	V
LDO Output-Voltage Accuracy	V _{BKSU} = 3.3V		MAX8568B	1.71	1.89	V

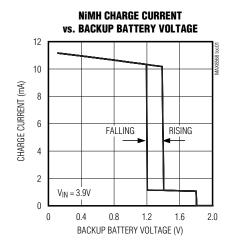
Note 1: All units are 100% production tested at $T_A = +25$ °C. Limits over the operating range are guaranteed by design.

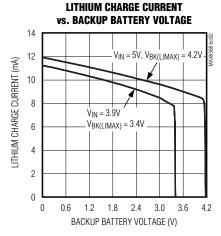
Note 2: All backup step-up converter specifications are with $V_{IN} = V_{INOK} = 0V$, unless otherwise noted.

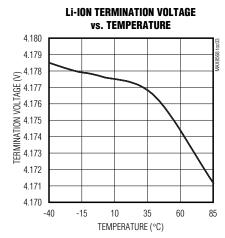
Note 3: Specifications to -40°C are guaranteed by design and not production tested.

Typical Operating Characteristics

(Circuit of Figure 7, VIN = 3.6V, VBK = 1.4V, VNI/LI = VBKSU = 3.3V, TA = +25°C, unless otherwise noted.)

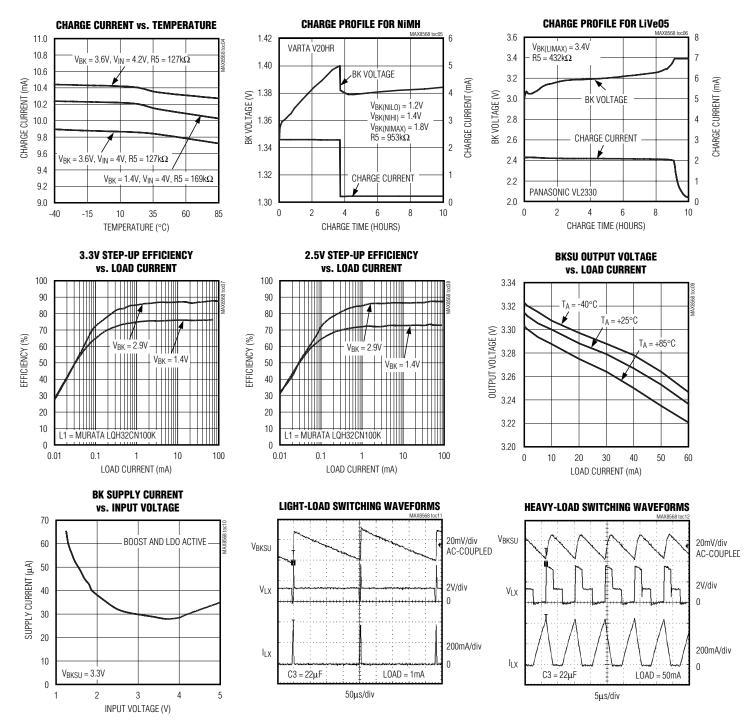






Typical Operating Characteristics (continued)

(Circuit of Figure 7, $V_{IN} = 3.6V$, $V_{BK} = 1.4V$, $V_{NI/LI} = V_{BKSU} = 3.3V$, $T_A = +25$ °C, unless otherwise noted.)

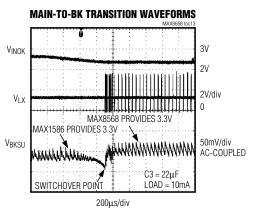


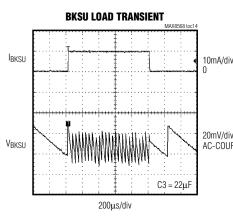
MAX8568A/MAX8568B

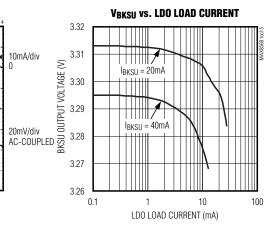
Complete Backup-Management ICs for Lithium and NiMH Batteries

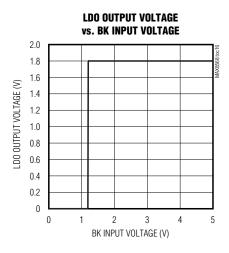
Typical Operating Characteristics (continued)

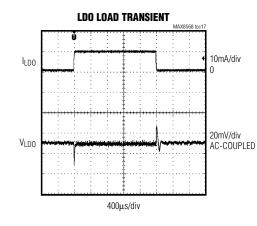
(Circuit of Figure 7, $V_{IN} = 3.6V$, $V_{BK} = 1.4V$, $V_{NI/LI} = V_{BKSU} = 3.3V$, $T_A = +25$ °C, unless otherwise noted.)

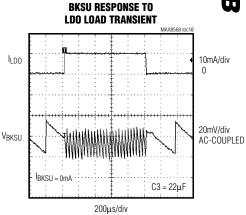


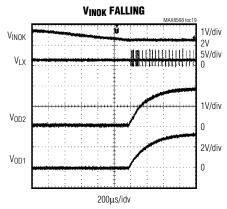


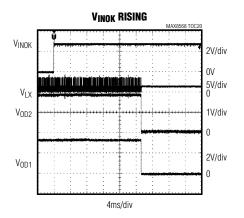












Pin Description

PIN	NAME	FUNCTION
1	IN	Main Battery Input. Connect to a 2.8V to 5.5V battery or other power source. Bypass with a 4.7µF ceramic capacitor to GND.
2	ВК	Backup Battery Input. Connect to an NiMH or rechargeable lithium backup battery. Connect a ceramic bypass capacitor from BK to GND. See the <i>Step-Up Capacitor Selection</i> section for more details.
3	PGND	Power Ground. Connect PGND to the ground side of the BK input capacitor and BKSU output capacitor. Use this connection as the star point for all grounds. See the <i>PC Board Layout and Routing</i> section for specific instructions regarding PGND.
4	LX	Inductor Connection for Low-I _Q Step-Up DC-DC Converter
5	BKSU	Step-Up Converter Output. Bypass with a 10µF to 22µF ceramic capacitor to PGND. The BKSU output voltage is set to either 3.3V or 2.5V without resistors, or to an adjustable voltage with an external resistor-divider. See the <i>Setting the Step-Up Converter Voltage</i> section.
6	LDO	2.5V (MAX8568A) or 1.8V (MAX8568B), 10mA LDO Output for Memory Supply. LDO is powered from BKSU. Bypass with a 4.7µF ceramic capacitor to GND.
7	OD1	11Ω Open-Drain Output. OD1 drives the gate of an external pMOS switch.
8	OD2	11Ω Open-Drain Output. OD2 drives the gate of an external pMOS switch.
9	NI/LI	Selects NiMH or Rechargeable Lithium Backup Battery. Connect NI/LI to BKSU if an NiMH backup battery is used. Connect NI/LI to GND if a rechargeable lithium backup battery is used.
10	BKV	Sets the BKSU Output Voltage. Connect to GND for 3.3V output at BKSU. Connect to BKSU for 2.5V output. Connect to the midpoint of a resistor-divider connected from BKSU to GND for adjustable output. See the Setting the Step-Up Converter Voltage section.
11	INOK	Main Battery Monitor. When V _{INOK} falls below 2.43V, charging stops and backup mode starts. The step-up converter and LDO turn on, and OD1 and OD2 go high impedance.
12	CHGI	Sets Backup Battery Charge Current. Connect a resistor from CHGI to GND to set the charge current. See the Setting the Charge Current section for details.
13	GND	Ground. Connect to the exposed paddle. Star all grounds at the BKSU output capacitor ground.
14	STRTV	Sets Fast-Charge Start Voltage for NiMH. See the Using an NiMH Backup Battery section.
15	TERMV	Sets Fast-Charge Stop Voltage for NiMH, as Well as the Battery Regulation Voltage for Both Rechargeable Lithium and Maximum Voltage for NiMH. See the <i>Using a Lithium Backup Battery</i> section and the <i>Using an NiMH Backup Battery</i> section.
16	REF	Reference Output. Bypass with a 0.22µF ceramic capacitor to GND.
EP	_	Exposed Paddle. Connect to the analog ground plane. EP also functions as a heatsink. Solder to the circuit-board analog ground plane.

Detailed Description

The MAX8568A/MAX8568B are compact ICs for managing backup battery charging and utilization in PDAs and other smart handheld devices. The MAX8568A/MAX8568B are comprised of three major blocks: 1) A multichemistry charger for small lithium-ion, lithium-manganese, LiVeO₅, and NiMH batteries; 2) a small very-low-current step-up DC-DC converter that generates a boosted backup supply when the backup battery output is less than required; and 3) an LDO that supplies a second backup voltage to an additional system block (typically low-voltage RAM).

Multichemistry Charger

The backup battery charger charges most types of rechargeable lithium and NiMH cells. Charging current can be set up to 25mA by a resistor connected from CHGI to GND. The charger operates a current-limited voltage source for rechargeable lithium batteries, and switches between fast and trickle charging for NiMH batteries.

NiMH Charging Scheme

The NiMH charger operates at two different charge currents based upon the voltages at TERMV and STRTV.

VSTRTV sets the BK voltage below which fast charging (set by CHGI) occurs. VTERMV sets the upper BK trip point where fast charging stops and trickle charging begins, and also sets a maximum voltage limit for the NiMH battery. If VTERMV is 1.2V, then fast charge stops at 1.2 / 0.86 = 1.4V, and the maximum voltage limit is 1.2 / 0.67 = 1.791V.

An NiMH battery fast charges until it hits 1.4V set by V_{TERMV}. The charger then switches to trickle charge at a current that is 10% of fast charge (set by CHGI). If the voltage drops (due to loading or self-discharge) to 1.2V (with V_{STRTV} = 1.2V), fast charge resumes. If the voltage then increases back to 1.4V (with V_{TERMV} = 1.2V), trickle charge resumes. If the cell voltage reaches 1.8V, the charge current falls to zero.

Lithium Charging Scheme

When charging rechargeable lithium-type batteries, VTERMV sets the charging voltage while VSTRTV is unused. Charge current is set by a resistor from CHGI to GND. There is no trickle charge for lithium mode. This charging scheme is essentially a current-limited voltage source.

Step-Up DC-DC Converter

If an NiMH battery or lower-voltage rechargeable lithium battery is used for backup, it may be necessary to boost the battery voltage to 2.5V, 3.3V, or some other voltage to power RAM, RTC, or other devices. The step-up DC-DC converter is powered by the backup battery but requires

that the I/O supply be activated at least one time before the backup battery can be stepped up. This allows the end product to draw no backup battery current while "on the shelf" waiting for its first activation. The step-up DC-DC converter is enabled, and reaches regulation, 50µs (typ) after INOK falls below 2.43V (typ).

The step-up converter includes a built-in synchronous rectifier that reduces cost by eliminating the need for an external diode and improves overall efficiency. The converter also features a clamp circuit that reduces EMI due to inductor ringing. The output voltage is set to 3.3V or 2.5V by connecting BKV to either GND or BKSU, respectively. For adjustable output, connect BKV to a resistor-divider from BKSU to GND.

LDO

For designs that require two different backup voltages, the MAX8568 includes a small LDO that is powered from BKSU. This LDO can supply up to 10mA and uses only 5µA of operating current. The LDO output is preset to 2.5V in the MAX8568A and 1.8V in the MAX8568B. The LDO is activated after VINOK falls below 2.43V (typ).

Switchover Behavior

See Figure 1 for switchover timing. If the backup battery is connected to the system before main power, the MAX8568 remains off and draws very little current, typically less than 0.5µA. This allows the end product to draw no backup battery current while "on the shelf" waiting for its first activation. When main power is connected, the MAX8568 powers on, assuming the main battery is greater than 2.8V. The MAX8568 begins to charge the backup battery if needed (see the *Multichemistry Charger* section). The OD1 and OD2 outputs pull to GND and turn on the external p-channel MOSFETs. This allows the voltage on I/O IN and MEM IN (Figure 7) to pass through to the I/O OUT and MEM OUT outputs. These I/O and MEM voltages are typically provided by a MAX1586/MAX1587 power-supply IC.

INOK monitors the main battery voltage and activates the backup boost converter and LDO when the voltage on VINOK falls below 2.43V. The backup converter starts 50µs after VINOK falls. OD1 and OD2 go high impedance and turn off the external p-channel MOSFETs. These MOSFETs disconnect the I/O IN and MEM IN inputs from the load. This ensures that the I/O and MEM main supplies do not draw current from the backup source (MAX8568). The charger also turns off when INOK is less than 2.43V.

If the MAX8568 is being evaluated as a stand-alone device, note that the backup-battery boost converter will not operate unless I/O IN has been activated at least one time. The typical power removal sequence for testing is 1) main battery goes low, then 2) MEM IN and I/O IN go low.

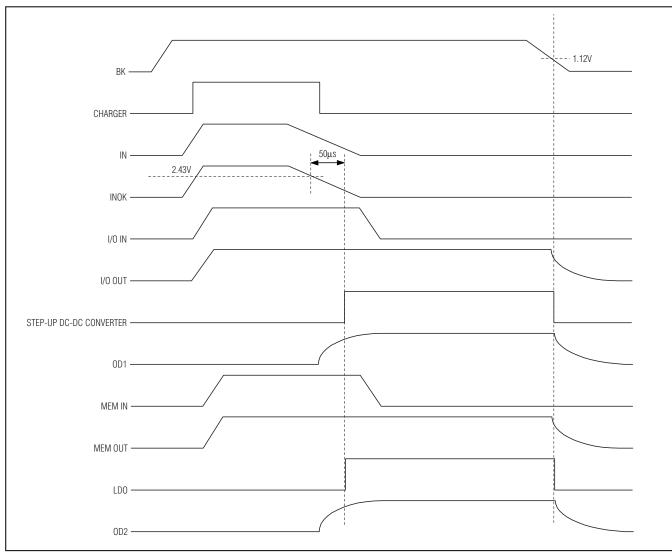


Figure 1. Timing Diagram

Applications Information Setting the Charge Current

Charge current is set by a resistor connected from CHGI to GND (R5 in Figure 7). The acceptable resistor range is from $50 k\Omega$ to $1800 k\Omega$. RCHGI is calculated by the following.

$$R_{CHGI}(k\Omega) = \left[\frac{41.2 \times (V_{IN} - V_{BK}) + 679.4}{I_{CHG}(mA)}\right]^{1.1641}$$

where VBK is the nominal voltage of the charged backup battery. This is the fast-charge current for both NiMH and lithium batteries. For NiMH batteries, the trickle charge is 10% of the fast-charge current.

Using a Rechargeable Lithium Backup Battery

The MAX8568 can charge a lithium-type backup battery from the main battery connected at IN. Connect NI/LI to GND for lithium backup battery charging. STRTV is unused and should be connected to GND in lithium charge mode.

The lithium charger acts like a current-limited voltage source. The battery regulation voltage for lithium mode, VBK(LIMAX), is:

 $V_{BK(LIMAX)} = 3.5 \times V_{TERMV}$

If $V_{TERMV} = 1.2V$, then the final charge voltage is 4.2V.

Connect TERMV to a resistor-divider from REF to GND. Adjust V_{TERMV} with resistors R11 and R12 (Figure 2). Select R12 to be in the $100\text{k}\Omega$ to $1\text{M}\Omega$ range. Calculate R11 as follows:

$$R11 = R12 \left(\frac{3.5 \times V_{REF}}{V_{BK(LIMAX)}} - 1 \right)$$

where $V_{REF} = 1.25V$.

Using an NiMH Backup Battery

The MAX8568 can charge NiMH backup batteries from the main battery connected at IN. Connect NI/LI to BKSU for NiMH backup battery charging. V_{TERMV} sets the maximum cell voltage and also the trip point for the fast-charge-to-trickle-charge transition. V_{STRTV} sets the trickle-to-fast-charge transition threshold.

In NiMH charge mode (NI/LI connected to BKSU), the charger ramps the battery between two thresholds measured at the battery connection BK, VBK(NILO) and VBK(NIHI). When the battery falls to VBK(NILO), trickle charging stops and fast charging starts. When the battery rises to VBK(NIHI), fast charging stops and trickle charging begins. If, for any reason, the battery contin-

ues to rise when trickle charged, all charging ceases at VBK(NIMAX). VBK(NILO), VBK(NIHI), and VBK(NIMAX) are set as follows:

BK voltage where fast charge begins:

 $V_{BK(NILO)} = V_{STRTV}$

BK voltage where trickle charge begins:

$$V_{BK(NIHI)} = 1.163 \times V_{TERMV}$$

BK voltage where all charging stops:

$$V_{BK(NIMAX)} = 1.493 \times V_{TERMV}$$

Resistor-dividers (see Figure 3) set V_{STRTV} and V_{TERMV} by dividing down REF. To minimize operating current, resistors between $100k\Omega$ and $1M\Omega$ should be used for R14 and R16 in Figure 3. The formulas for the upper divider-resistors in terms of V_{BK(NILO)}, V_{BK(NIHI)}, and V_{BK(NIMAX)} are:

$$R13 = R14 \left(\frac{V_{REF}}{V_{BK(NILO)}} - 1 \right)$$

$$R15 = R16 \left(\frac{1.163 \times V_{REF}}{V_{BK(NIHI)}} - 1 \right)$$

Once $V_{BK(NIHI)}$ is selected, the maximum battery voltage is:

$$V_{BK(NIMAX)} = 1.283 \times V_{BK(NIHI)}$$

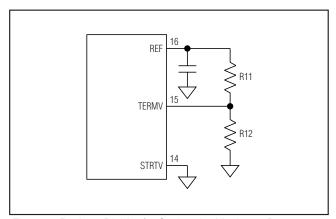


Figure 2. Resistor-Divider for Setting the Maximum Battery Voltage, V_{BK(LIMAX)}, for Rechargeable Lithium-Type Backup Batteries

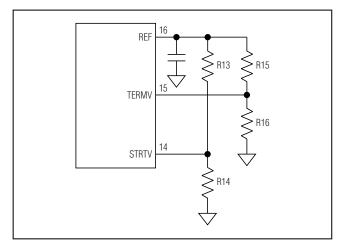


Figure 3. 2-Resistor-Dividers for Setting V_{BK(NILO)} and V_{BK(NIHI)}

Note that both $V_{BK(NILO)}$ and $V_{BK(NIHI)}$ can be set with a 2-resistor voltage-divider as shown in the typical application circuit (see Figure 7) if the factory-set ratio between the two thresholds is acceptable. In that case:

$$R6 = R8 \left(\frac{V_{REF}}{V_{BK(NILO)}} - 1 \right)$$

 $V_{BK(NIHI)} = 1.163 \times V_{BK(NILO)}$ $V_{BK(NIMAX)} = 1.283 \times V_{BK(NIHI)}$

One 3-resistor-divider can be used to set both VBK(NILO) and VBK(NIHI) independently. Figure 4 shows the connections of R17, R18, and R19. Select R19 in the $100k\Omega$ to $1M\Omega$ range. The equations for the two upper divider-resistors are:

$$R18 = R19 \left(\frac{V_{REF}}{V_{BK(NILO)}} - 1 \right)$$

R17 = (R18 + R19)
$$\times \left(\frac{1.163 \times V_{REF}}{V_{BK(NIHI)}} - 1\right)$$

Setting the Switchover Voltage

VINOK sets the IN voltage at which backup mode starts. INOK connects to a resistor-divider between IN and GND. The MAX8568 requires VIN greater than 2.8V for proper operation when not backing up, so the backup threshold, VIN(BACKUP), must be set for no less than 2.8V. Once VINOK drops below 2.43V (typ), VIN may be less than 2.8V. The resistor-divider for INOK is shown in Figure 7 (R9 and R10). Select resistor R10 to be in the $100 k\Omega$ to $1 M\Omega$ range. Calculate R9 as follows:

$$R9 = R10 \left(\frac{V_{IN(BACKUP)}}{V_{INOK}} - 1 \right)$$

where $V_{INOK} = 2.43V$, and $V_{IN(BACKUP)}$ must be set greater than 2.8V.

Step-Up Converter

The step up DC-DC converter is most likely used with NiMH backup batteries, but can also be used with rechargeable lithium backup batteries. If the backup battery voltage is greater than the set output voltage at BKSU, the output voltage follows the backup battery voltage. The voltage difference between the backup battery and BKSU never exceeds a diode forward-voltage drop. If I/O OUT (Figure 7) is less than BK during charge mode, no current flows from BK to I/O OUT.

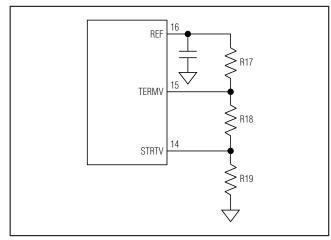


Figure 4. 3-Resistor Divider Used to Set VBK(NILO) and VBK(NIHI)

Step-Up Capacitor Selection

Choose output capacitors to supply output peak currents with acceptable voltage ripple. Low equivalent-series-resistance (ESR) capacitors are recommended. Ceramic capacitors have the lowest ESR, but low-ESR tantalum or polymer capacitors offer a good balance between cost and performance.

Output voltage ripple has two components: variations in the charge stored in the output capacitor with each LX pulse and the voltage drop across the capacitor's ESR caused by the current into and out of the capacitor. The equations for calculating output ripple are:

$$V_{RIPPLE(C)} = \frac{1}{2} \left(\frac{L}{(V_{BKSU} - V_{BK})C_{BKSU}} \right) I_{PEAK}^{2}$$

where IPEAK is the peak inductor current (see the *Inductor Selection* section). For ceramic capacitors, the output voltage ripple is typically dominated by VRIPPLE(C).

Input capacitors connected to IN and BK should be X5R or X7R ceramic capacitors. C_{IN} should be 4.7 μ F or greater. C_{BK} should be 10 μ F or greater when using the step-up converter. If the step-up converter is not used, then C_{BK} can be reduced to 1 μ F.

Capacitance and ESR variation with temperature should be considered for best performance in applications with wide operating temperature ranges.

Inductor Selection

The control scheme of the MAX8568 permits flexibility in choosing an inductor. A 10µH inductor performs well in most applications. Smaller inductance values typically offer smaller physical size for a given series resistance, allowing the smallest overall circuit dimensions. Circuits using larger inductance may provide higher efficiency and exhibit less ripple, but also may reduce the maximum output current. This occurs when the inductance is sufficiently large to prevent the LX current limit (ILIM) from being reached before the maximum on-time (ton(MAX)) expires.

For maximum output current, choose the inductor value so that the controller reaches the current limit before the maximum on-time is reached:

$$L < \frac{V_{BK} \times t_{ON(MAX)}}{I_{LIM}}$$

where ton(MAX) is typically 5µs, and the current limit (ILIM) is typically 500mA (see the *Electrical Characteristics* table).

For larger inductor values, determine the peak inductor current (IPEAK) by:

$$I_{PEAK} = \frac{V_{BK} \times t_{ON(MAX)}}{L}$$

Setting the Output Voltage

The output voltage is set to 2.5V or 3.3V, or is adjustable. Connect BKV to GND for 3.3V, and BKV to BKSU for 2.5V. The adjustable output voltage is set from 2.5V to 5V using external resistors R1 and R2 (Figure 7). Since FB leakage is 50nA (max), select feedback resistor R2 in the $100k\Omega$ to $1M\Omega$ range. Calculate R1 as follows:

$$R1 = R2 \left(\frac{V_{BKSU}}{V_{BKV}} - 1 \right)$$

where $V_{BKV} = 1.21V$.

LDO

The LDO output voltage is preset to 2.5V for the MAX8568A and 1.8V for the MAX8568B. The LDO can supply up to 10mA. The LDO output voltage is not adjustable.

LDO Capacitor Selection

Capacitors are required at the LDO output of the MAX8568 for stable operation over the full load and temperature range. A 4.7 μ F or greater X5R or X7R ceramic capacitor is recommended. To reduce noise and improve load-transient response, larger output capacitors up to 10 μ F can be used. Surface-mount ceramic capacitors have very low ESR and are commonly available in values up to 10 μ F. Note that some ceramic dielectrics, such as Z5U and Y5V, exhibit large capacitance and ESR variation with temperature and require larger than the recommended values to maintain stability and good load-transient response over temperature.

External MOSFET Drivers—OD1, OD2

OD1 and OD2 are open-drain outputs and are designed to be connected to the gates of external pchannel MOSFETs (see Figure 7). These MOSFETs connect the main system power supplies (I/O IN and MEM IN) to the system loads (I/O OUT and MEM OUT) during normal operation. During backup, they disconnect the power supplies from the system loads to prevent the power supplies from drawing backup current away from the system. For this reason, the MOSFETs are connected "backwards" from what might be expected. The source of the MOSFETs are connected to the system load side (I/O OUT and MEM OUT). The MOSFETs' purpose is to block current flow from the backup supply (BKSU) to the main supplies (I/O IN and MEM IN). They do not block current flow from I/O IN to I/O OUT and from MEM IN to MEM OUT. Even when off, the MOSFET body diodes allow current to pass in that direction.

OD1 is intended to drive the MOSFET switch for I/O IN and I/O OUT, while OD2 is intended to drive the MOSFET switch for MEM IN and MEM OUT. See the Typical Operating Characteristics and Figure 1 for typical operation of OD1 and OD2.

External MOSFET Selection

The external MOSFET should be chosen based upon RDS(ON) and gate capacitance. When $V_{\rm INOK} > 2.43V$ (main battery > 2.8V), the current required for normal operation of I/O and MEM goes through these external MOSFETs. Choose an RDS(ON) that minimizes the MOSFET voltage drop. When $V_{\rm INOK} < 2.43V$, the MOSFET turns off, and MEM and I/O are powered by the MAX8568. The gate capacitance of the external MOSFET must discharge through the external gate-to-source resistor. This discharge time determines how quickly the main supply is disconnected and isolated.

Pullup resistors, R3 and R4 in Figure 7, should be selected to ensure that when OD1 and OD2 go high impedance, the gate of the external MOSFET discharges within 50µs to 100µs. This time allows the backup converters to start and provide power to I/O and MEM. Discharges longer than 50µs to 100µs could cause the main supply to back drain current from the MAX8568 and allow the I/O OUT and MEM OUT voltage to droop. The MOSFET gate-source resistor, RGS, is calculated from the following formulas:

$$\tau = RGS \times CISS$$

$$\tau = \frac{-50\mu s}{ln\left(1 - \frac{V_{GS(TH)}}{V_{BKSU}}\right)}$$

where the MOSFET gate-source threshold, V_{GS(TH)}, and MOSFET input capacitance, C_{ISS}, are provided on the MOSFET data sheet.

Connection with MAX1586

When the MAX8568 is used with the MAX1586 system power supply, it may be preferable to employ the MAX1586's voltage monitors to determine when backup should start. The connection for this is shown in Figure 5 where the dead-battery output (DBO) of the MAX1586 drives the INOK input of the MAX8568. This, in effect, overrides the voltage-sensing circuit on the MAX8568 and uses the DBO monitor on the MAX1586. Refer to the MAX1586 data sheet for information on how to set the DBO threshold. The CHG connection in Figure 5 is described in the next section.

Terminating Charging at a Voltage Other than the Switchover Voltage

In normal operation, the MAX8568 charger is always active as long as the INOK voltage is valid (above 2.43V). In some systems, however, it may be desirable to terminate backup battery charging when the main battery is somewhat depleted but not so low as to trigger backup. An external voltage monitor, or a voltage monitor in a power-supply IC, such as the MAX1586, can disable charging by disconnecting the CHGI resistor. If CHGI is open, no charging current flows. This can be accomplished with the circuit in Figure 5. The low-battery output (LBO) of the MAX1586 pulls low when the battery falls below a user-set level (refer to the MAX1586 data sheet). This turns off the external n-channel MOSFET (or

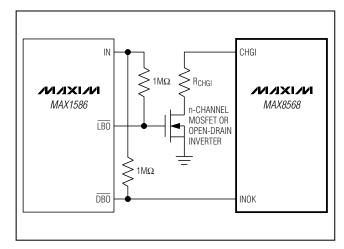


Figure 5. Using a MAX1586 Power-Supply IC to Trigger Backup Switchover and to Disable Backup Battery Charging Prior to Switchover

open-drain logic inverter) and disconnects the current path through R_{ICHG}. Backup charging can be stopped for any reason using this method.

PC Board Layout and Routing

Careful PC board layout is important for minimizing ground bounce and noise. Ensure that C1 (IN input capacitor), C2 (BK input capacitor), C3 (BKSU bypass capacitor), and C4 (LDO output capacitor) are as close as possible to the IC. Avoid using vias to connect C2 or C3 to their respective pins or GND. C2 and C3 grounds should be next to each other, and this connection can then be used as the star ground point. All other grounds should connect to the star ground. PGND should star at C2 and C3, and should not connect directly to the exposed pad (EP) of the MAX8568. Connect EP to the bottom layer ground plane, and then connect the ground plane to the star ground. Vias on the inductor path are acceptable if necessary. IN, BK, BKSU, and LDO traces should be as wide as possible to minimize inductance. Refer to the MAX8568 evaluation kit for a PC board layout example.

Chip Information

TRANSISTOR COUNT: 7902

PROCESS: BICMOS

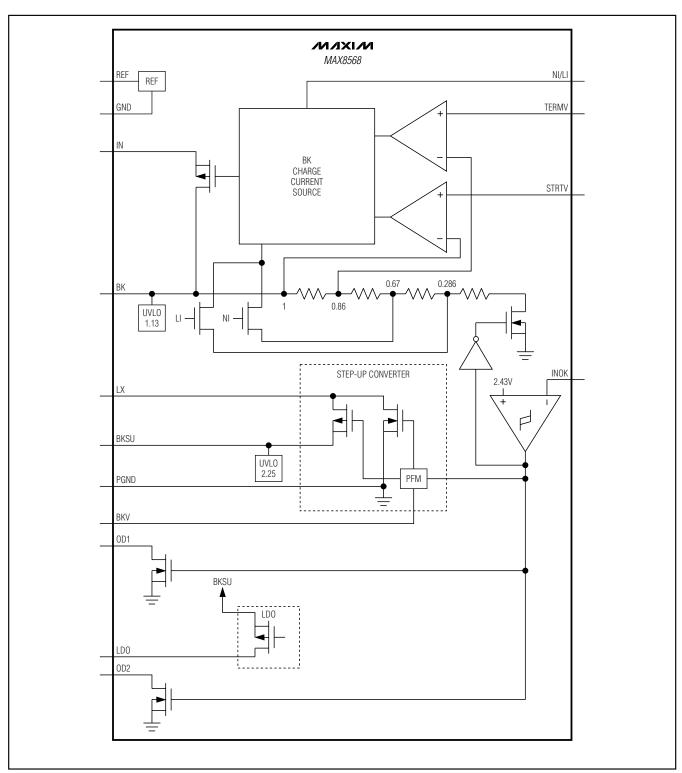


Figure 6. Functional Diagram

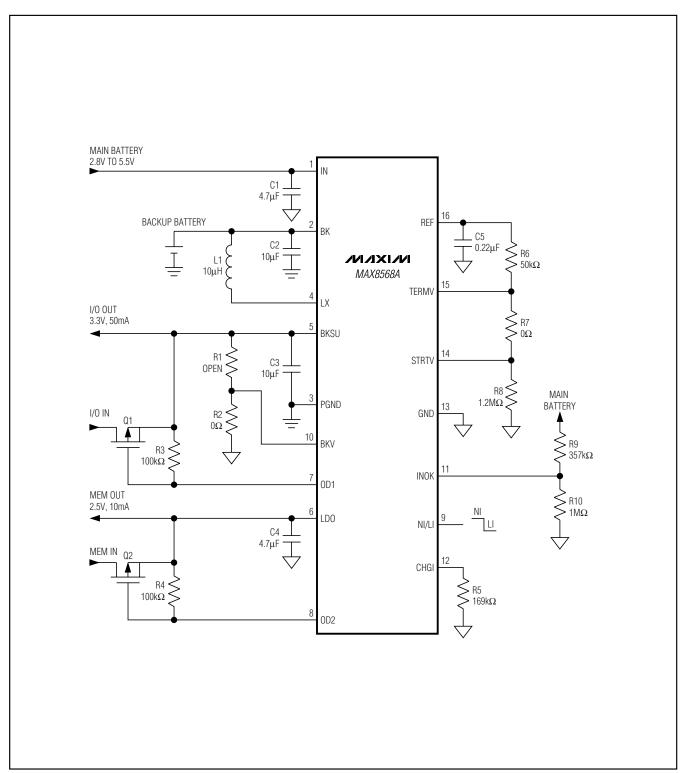
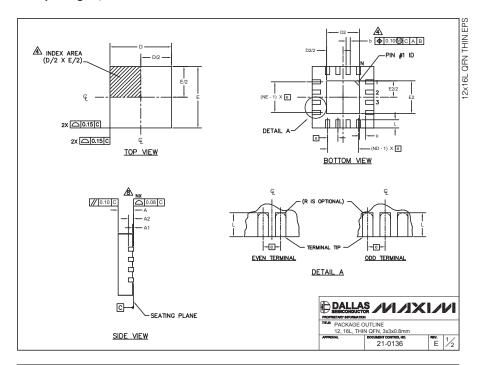


Figure 7. Typical Application Circuit

Package Information)

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to www.maxim-ic.com/packages.)



PKG		12L 3x3			16L 3x3	
REF.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX
Α	0.70	0.75	0.80	0.70	0.75	0.80
b	0.20	0.25	0.30	0.20	0.25	0.30
D	2.90	3.00	3.10	2.90	3.00	3.10
E 2.90 3.00 3	3.10	1.10 2.90	3.00	3.10		
е		0.50 BSC			0.50 BSC	
L	0.45	0.55	0.65	0.30	0.40	0.50
N		12	16			
ND		3		4		
NE		3			4	
A1	0	0.02	0.05	0	0.02	0.05
A2		0.20 REF			0.20 REF	
k	0.25	0.25			-	-

EXPOSED PAD VARIATIONS									
PKG.		D2			E2		PIN ID	JEDEC	DOWN BONDS
CODES	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	FINID	JEDEC	ALLOWED
T1233-1	0.95	1.10	1.25	0.95	1.10	1.25	0.35 x 45∞	WEED-1	NO
T1233-3	0.95	1.10	1.25	0.95	1.10	1.25	0.35 x 45∞	WEED-1	YES
T1633-1	0.95	1.10	1.25	0.95	1.10	1.25	0.35 x 45∞	WEED-2	NO
T1633-2	0.95	1.10	1.25	0.95	1.10	1.25	0.35 x 45∞	WEED-2	YES
T1633F-3	0.65	0.80	0.95	0.65	0.80	0.95	0.225 x 45∞	WEED-2	N/A
T1633-4	0.95	1.10	1.25	0.95	1.10	1.25	0.35 x 45∞	WEED-2	NO

NOTES:

- 1. DIMENSIONING & TOLERANCING CONFORM TO ASME Y14.5M-1994
- 2. ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES 3. N IS THE TOTAL NUMBER OF TERMINALS.
- ATHE TERMINAL #1 IDENTIFIER AND TERMINAL NUMBERING CONVENTION SHALL CONFORM TO JESD 95-1 SPP-012. DETAILS OF TERMINAL #1 IDENTIFIER ARE OPTIONAL, BUT MUST BE LOCATED WITHIN THE ZONE INDICATED. THE TERMINAL #1 IDENTIFIER ARY BE EITHER A MOLD OR MARKED FEATURE.
- A DIMENSION & APPLIES TO METALLIZED TERMINAL AND IS MEASURED BETWEEN 0.20 mm AND 0.25 mm FROM TERMINAL TIP.
- ⚠ ND AND NE REFER TO THE NUMBER OF TERMINALS ON EACH D AND E SIDE RESPECTIVELY
- DEPOPULATION IS POSSIBLE IN A SYMMETRICAL FASHION.

9. DRAWING CONFORMS TO JEDEC MO220 REVISION C.



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